

#### **Description**

The SQ4410EY-T1\_GE3 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

### **General Features**

 $V_{DS} = 30V I_{D} = 15A$ 

 $R_{DS(ON)} < 10m\Omega$  @  $V_{GS}=10V$ 

# **Application**

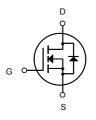
Battery protection

Load switch

Uninterruptible power supply



SOP-8 (SO-8)



N-Channel MOSFET

## **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
SQ4410EY-T1_GE3	SOP-8(SO-8)	HXY MOSFET	3000

# Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current <sup>1</sup>	15	А
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current <sup>1</sup>	8	А
МФІ	Pulsed Drain Current <sup>2</sup>	45	А
EAS	Single Pulse Avalanche Energy <sup>3</sup>	12	mJ
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>4</sup>	15	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
_	Thermal Resistance Junction-ambient¹(t≤10s)	85	°C/W
R <sub>θ</sub> JA	Thermal Resistance Junction-ambient <sup>1</sup>	25	°C/W

## N-Channel Enhancement Mode MOSFET

# Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	in-Source Breakdown Voltage V <sub>GS</sub> =0V , I <sub>D</sub> =250uA				V	
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA		0.034		V/°C	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}$ =10V , $I_D$ =7A		8	10	m()	
NDS(ON)	Static Dialii-Source On-Resistance	V <sub>GS</sub> =4.5V , I <sub>D</sub> =4A	1	12	15	mΩ	
$V_{GS(th)}$	Gate Threshold Voltage	ate Threshold Voltage		1.4	2.5	V	
$\triangle V_{GS(th)}$	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA			-3.84		mV/°C	
1	Drain-Source Leakage Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	- uA	
I <sub>DSS</sub>		V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C			5		
Igss	Gate-Source Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}=0V$			±100	nA	
gfs	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =7A		6.2		S	
Rg	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		1.04	2.1	Ω	
Qg	Total Gate Charge (4.5V)			6	8.4		
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =15V , V <sub>GS</sub> =4.5V , I <sub>D</sub> =7A		2.2	3.1	nC	
Q <sub>gd</sub>	Gate-Drain Charge			2	2.8		
T <sub>d(on)</sub>	Turn-On Delay Time			1.2	2.4	ns	
Tr	Rise Time	$V_{DD}$ =15V , $V_{GS}$ =10V , $R_{G}$ =3.3 $\Omega$		40	72.0		
T <sub>d(off)</sub>	Turn-Off Delay Time	I <sub>D</sub> =7A		18	36.0		
Tf	Fall Time			7.2	14.4		
Ciss	Input Capacitance			983	1616		
Coss	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		147	207.8	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance	e Transfer Capacitance		109	162.6		
Is	Continuous Source Current <sup>1,5</sup>	V V 0V 5 0			15	Α	
Ism	Pulsed Source Current <sup>2,5</sup> V <sub>G</sub> =V <sub>D</sub> =0V , Force Current				35	Α	
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup> V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C				1.2	V	
t <sub>rr</sub>	Reverse Recovery Time			7.2		nS	
Qrr	Reverse Recovery Charge	lF=7A , dl/dt=100A/μs , T <sub>J</sub> =25°C		2.9		nC	

- 1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%
- 3. The EAS data shows Max. rating . The test condition is  $V_{DD}$ =25V,  $V_{GS}$ =10V, L=0.1mH,  $I_{AS}$ =20A
- 4. The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

# **Typical Characteristics**

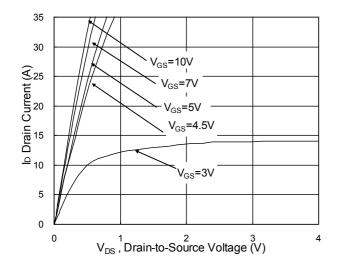


Fig.1 Typical Output Characteristics

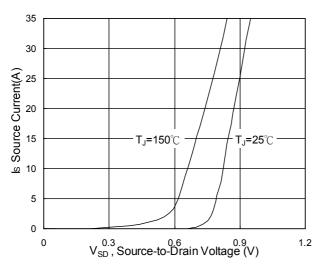


Fig.3 Forward Characteristics Of Reverse

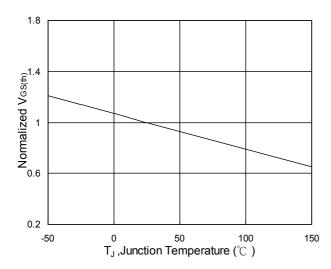


Fig.5 Normalized  $V_{\text{GS(th)}}$  vs.  $T_{\text{J}}$ 

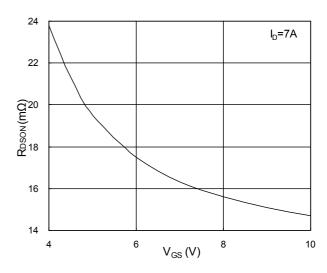


Fig.2 On-Resistance vs. Gate-Source

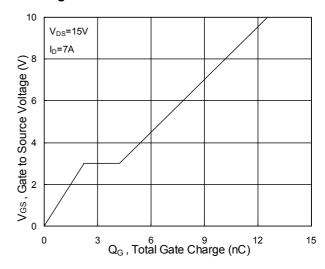


Fig.4 Gate-Charge Characteristics

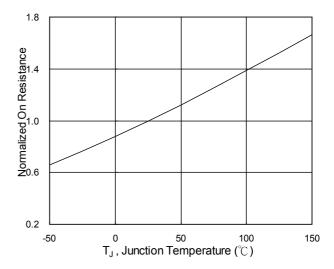
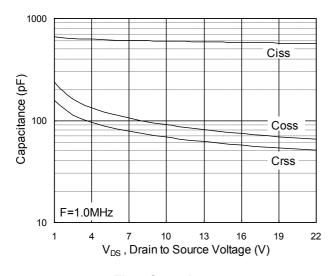


Fig.6 Normalized R<sub>DSON</sub> vs. T<sub>J</sub>





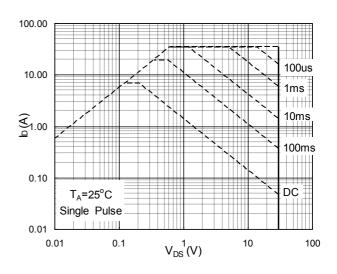


Fig.7 Capacitance

Fig.8 Safe Operating Area

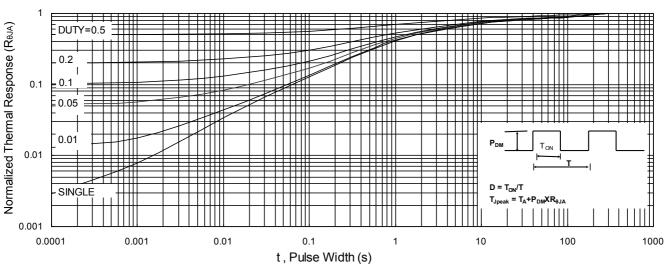


Fig.9 Normalized Maximum Transient Thermal Impedance

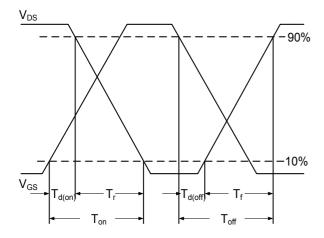


Fig.10 Switching Time Waveform

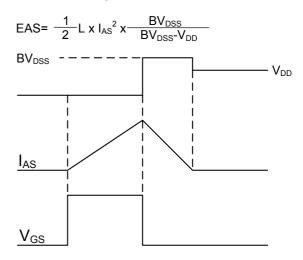
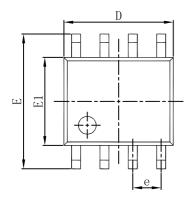
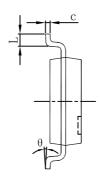
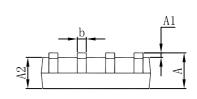


Fig.11 Unclamped Inductive Switching Waveform

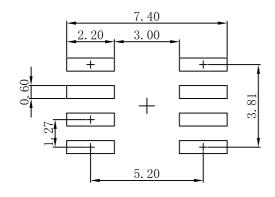
# **SOP-8(SO-8) Package Outline Dimensions**







Symbol	Dimensions In Millimeters		Dimensions In Inches			
Symbol	Min	Max	Min	Max		
A	1. 350	1.750	0.053	0.069		
A1	0.100	0. 250	0.004	0.010		
A2	1.350	1.550	0.053	0.061		
b	0.330	0.510	0.013	0. 020		
c	0.170	0.250	0.007	0.010		
D	4.800	5.000	0.189	0.197		
e	1. 270 (	1. 270 (BSC)		0.050 (BSC)		
E	5.800	6.200	0.228	0.244		
E1	3.800	4.000	0.150	0.157		
L	0.400	1.270	0.016	0.050		
θ	0°	8°	0°	8°		



- Note: 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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